

SILICON TRANSISTOR 2SC3356

PACKAGE DIMENSIONS

(Units: mm)

MICROWAVE LOW NOISE AMPLIFIER NPN SILICON EPITAXIAL TRANSISTOR

DESCRIPTION

The 2SC3356 is an NPN silicon epitaxial transistor designed for low noise amplifier at VHF, UHF and CATV band.

It has dynamic range and good current characteristic.

FEATURES

· Low Noise and High Gain

NF = 1.1 dB TYP., Ga = 11 dB TYP. @VcE = 10 V, Ic = 7 mA, f = 1.0 GHz

· High Power Gain

MAG = 13 dB TYP. @VcE = 10 V, Ic = 20 mA, f = 1.0 GHz

ABSOLUTE MAXIMUM RATINGS (TA = 25 °C) Collector to Base Voltage 20 12 Collector to Emitter Voltage √ceo Emitter to Base Voltage Collector Current lс 100 mΑ Рτ 200 **Total Power Dissipation** mW Junction Temperature 150 °C Τj Storage Temperature Tstg -65 to +150 °C

2.8±0.2 1.5 O.65*-0.15 O.65

ELECTRICAL CHARACTERISTICS (TA = 25 °C)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Collector Cutoff Current	Ісво			1.0	μА	Vcb = 10 V, IE = 0
Emitter Cutoff Current	Іево			1.0	μА	VEB = 1.0 V, Ic = 0
DC Current Gain	h _{FE} *	50	120	300		Vce = 10 V, Ic = 20 mA
Gain Bandwidth Product	f⊤		7		GHz	Vce = 10 V, Ic = 20 mA
Feed-Back Capacitance	Cre**		0.55	1.0	pF	VcB = 10 V, IE = 0, f = 1.0 MHz
Insertion Power Gain	S ₂₁ e ²		11.5		dB	Vce = 10 V, Ic = 20 mA, f = 1.0 GHz
Noise Figure	NF		1.1	2.0	dB	Vce = 10 V, Ic = 7 mA, f = 1.0 GHz

Pulse Measurement PW ≤ 350 μs, Duty Cycle ≤ 2 %

hre Classification

nfe Classification							
Class	R23/Q *	R24/R *	R25/S *				
Marking	R23	R24	R25				
hfe	50 to 100	80 to 160	125 to 250				

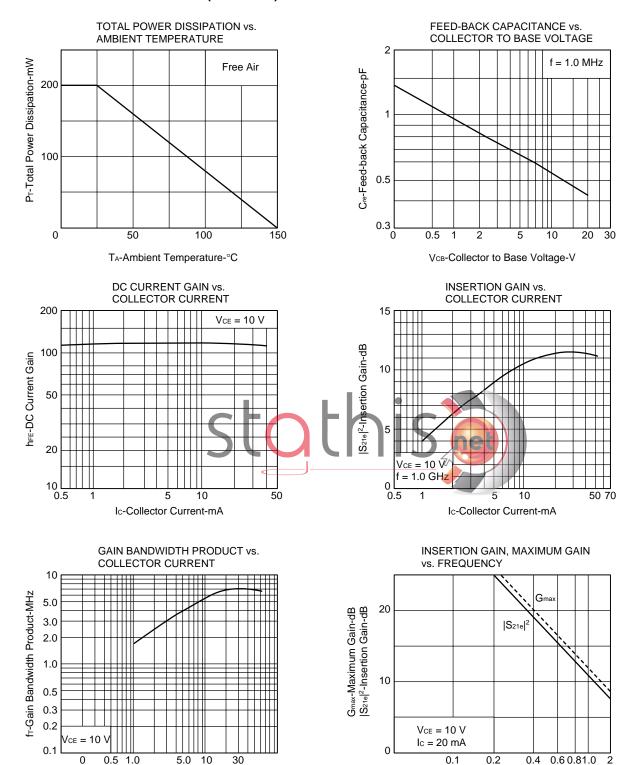
Old Specification / New Specification

The emitter terminal and the case shall be connected to the guard terminal of the three-terminal capacitance bridge.



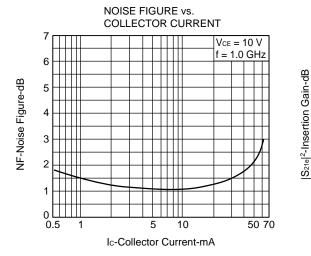
TYPICAL CHARACTERISTICS (TA = 25 °C)

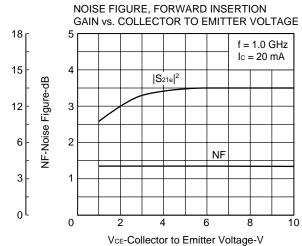
Ic-Collector Current-mA



f-Frequency-GHz







S-PARAMETER

Vce = 10 V, Ic = 5 mA, Zo = 50 Ω

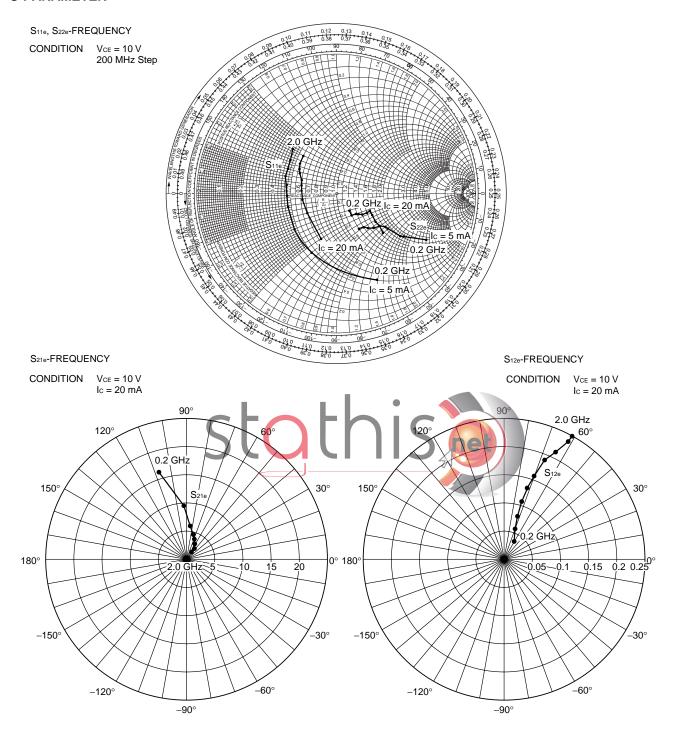
f (MHz)	S ₁₁	∠ S 11	S ₂₁	∠ S 21	S ₁₂	∠ S ₁₂	S ₂₂	∠ S 22
200	0.651	-69.3	10.616	129.3	0.051	59.2	0.735	-28.1
400	0.467	-113.3	6.856	104.4	0.071	54.4	0.550	-34.1
600	0.391	-139.3	4.852	90.9	0.086	56.0	0.468	-33.9
800	0.360	-159.2	3.802	81.2	0.101	59.1	0.426	-33.6
1000	0.360	-176.9	3.098	72.9	0.118	61.0	0.397	-35.7
1200	0.361	172.7	2.646	67.3	0.137	63.5	0.373	-38.3
1400	0.381	160.3	2.298	59.3	0.157	63.3	0.360	-43.0
1600	0.398	152.2	2.071	55.2	0.180	64.1	0.337	-45.9
1800	0.423	143.3	1.836	49.0	0.263	63.7	0.320	-52.3
2000	0.445	137.6	1.689	46.2	0.220	64.7	0.302	-52.2

 V_{CE} = 10 V, Ic = 5 mA, Zo = 50 Ω

f (MHz)	S ₁₁	∠ S 11	S ₂₁	∠ S 21	S ₁₂	∠ S 12	S22	∠ S 22
200	0.339	-107.0	16.516	108.7	0.035	66.1	0.459	-36.6
400	0.258	-147.3	8.928	92.1	0.060	71.0	0.343	-32.9
600	0.243	-167.7	6.022	83.0	0.085	71.9	0.305	-29.9
800	0.242	177.0	4.633	76.2	0.109	72.2	0.284	-29.4
1000	0.260	164.5	3.744	69.9	0.136	70.4	0.266	-31.7
1200	0.269	157.6	3.193	65.7	0.160	69.9	0.246	-35.0
1400	0.294	148.7	2.750	58.8	0.187	66.7	0.233	-40.4
1600	0.314	143.1	2.479	55.5	0.212	65.2	0.208	-43.6
1800	0.343	136.5	2.185	50.1	0.238	62.4	0.190	-50.5
2000	0.367	131.4	2.016	47.8	0.254	61.6	0.173	-48.3



S-PARAMETER



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Anti-radioactive design is not implemented in this product.

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